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Technical Note

1970-27

On the Theory of Localized
One-Electron States
in Perfect Crystals

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1 September 1970

Prepared under Electronic Systems Division Contract AF 19(628)-5167 by

Lincoln Laboratory

MASSACHUSETTS INSTITUTE OF TECHNOLOGY

Lexington, Massachusetts



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ON THE THEORY OF LOCALIZED ONE-ELECTRON STATES
IN PERFECT CRYSTALS

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TECHNICAL NOTE 1970-27

1 SEPTEMBER 1970

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The work reported in this document was performed at Lincoln Laboratory, a center for research operated by Massachusetts Institute of Technology, with the support of the Department of the Air Force under Contract AF 19(628)-5167.

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ABSTRACT

In a recent paper a proof was given that for a perfect crystal of hydrogen atoms, described within a certain model, the free energy corresponding to localized one-electron wavefunctions was less than that corresponding to spatially extended one-electron functions. That proof, however, depended on the assumption that the summand a_ℓ appearing in the partition function for the extended solutions monotonically increases with ℓ for $\ell \gg 0$. The proof of this monotonicity is given here.

Accepted for the Air Force
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Chief, Lincoln Laboratory Project Office

1. INTRODUCTION

In a recent paper¹ (to which we shall refer as I), a proof was given that for a perfect crystal of hydrogen atoms, described within a certain model, the free energy corresponding to localized one-electron functions was less than that corresponding to spatially extended one-electron functions [eq. (I3.25), i.e. eq. (3.25) of I]. These terms were defined in the framework of a new variational approximation in statistical mechanics, the thermal single-determinant approximation,² and under certain specified limitations on the model discussed in detail in I. This result was a central one in that paper,¹ and therefore rigor in the proof was strived for. However, the proof given (Appendix A of I) depended on the assumption (made plausible there) that the summand a_ℓ appearing in the partition function for the extended solutions [eqs. (IA.9), (IA.10)] monotonically increases with ℓ for $\ell \geq 0$. The proof of this monotonicity is presented in this report.

1. T. A. Kaplan and P. N. Argyres, Phys. Rev. B 1, 2457 (1970).

2. T. A. Kaplan, Bull. Am. Phys. Soc. 13, 386 (1968) and Solid State Research Report No. DDC-AD672961, Lincoln Laboratory, M.I.T. (1968:2) p. 53.

2. PROOF OF THE MONOTONICITY OF a_ℓ

For completeness we start with the definitions

$$a_\ell = \binom{N}{\frac{1}{2}N + \ell} \left(\cosh \frac{x\ell}{N} \right)^N \quad (2.1)$$

$$g_\ell \equiv \frac{a_{\ell+1}}{a_\ell} \quad (2.2)$$

ℓ is an integer. (N is used here in place of \mathcal{N} appearing in I.)

We shall prove $a_\ell \leq a_{\ell+1}$ for $0 \leq \ell \leq \frac{N}{2} - 1$. Thus putting

$$\frac{\ell}{N} = y \quad (2.3)$$

and

$$\ln g_\ell = h(y) \quad (2.4)$$

we need to show that $h(y) \geq 0$ for $0 \leq y \leq \frac{1}{2} - \frac{1}{N}$, in steps of $1/N$.

Equation (IA.12) gives

$$h(y) = N \ln \cosh \frac{x}{N} + N \ln (1 + \tanh \frac{x}{N} \tanh xy) + \ln \frac{1 - 2y}{1 + 2y + \frac{1}{N}} \quad (2.5)$$

But $\ln \cosh \frac{x}{N} \geq 0$, and, for $a \geq 0$,

$$\ln (1+a) \geq a - \frac{a^2}{2} \quad (2.6)$$

and

$$\ln(1+a) \leq a \quad (2.7)$$

Thus

$$h(y) \geq N \left(\tanh \frac{x}{N} \tanh xy - \frac{1}{2} \tanh^2 \frac{x}{N} \right) + \ln \frac{1-2y}{1+2y} - \frac{1}{N(1+2y)} \quad (2.8)$$

But

$$\tanh a \leq a, \quad a \geq 0 \quad (2.9)$$

so that (2.8) gives

$$h(y) \geq N \tanh \frac{x}{N} \tanh xy + \ln \frac{1-2y}{1+2y} - \frac{x^2}{2N} - \frac{1}{N(1+2y)} \quad (2.10)$$

Using (IA.27), then

$$h(y) \geq x \tanh xy - \ln \frac{1+2y}{1-2y} - \frac{x^2}{2N} - \frac{x^3}{3N^2} - \frac{1}{N} \quad (2.11)$$

or

$$h(y) \geq \gamma(y) - \varepsilon \equiv h_0(y) \quad (2.12)$$

where

$$\gamma(y) = x \tanh xy - \ln \frac{1+2y}{1-2y} \quad (2.13)$$

$$\varepsilon = \frac{x^2}{2N} + \frac{x^3}{3N^2} + \frac{1}{N} \quad (2.14)$$

The equation $\gamma(y) = 0$ arises in the thermal Hartree-Fock approximation. It is easy to see graphically (see Fig. 1) and one can show analytically that there are at most three roots $y = 0, \pm \tilde{y}$, for $|\tilde{y}| \leq 1/2$; also the condition for the occurrence of three

roots is $x > 2$. So if we could drop ε , then we would know that $h(y) > 0$ for all y in the range 0 to \tilde{y} . Furthermore, \tilde{y} turns out, for x as big as 100, to be extremely close to $1/2$, so close that $N(\frac{1}{2} - \tilde{y}) \ll 1$, so we would then have completed the proof. But we have $\varepsilon \neq 0$. The functions $x \tanh xy$ and $\ln \frac{1+2y}{1-2y}$ are shown qualitatively in Fig. 1, which is drawn for $x^2 > 4$.

Our argument is as follows. We will first show that $h(y) > 0$ for $y = \frac{1}{2} - \frac{1}{N}$, i.e. for $\ell = \frac{N}{2} - 1$ (note that for $\ell = N/2$, i.e. $y = 1/2$, $h(\frac{1}{2}) = -\infty$); that is, at the first integral step (in ℓ) towards the left from $y = 1/2$, one has passed the first crossing of $x \tanh xy$ and $\ln \frac{1+2y}{1-2y} + \varepsilon$. It is clear (from the figure) then that $h(y)$ will remain positive as y decreases until $y = y_0$, (small and positive) is reached. We will obtain an upper bound on y_0 of $2/N$. Finally we will show that g_0 and g_1 are > 1 and this will conclude the proof that $a_\ell \leq a_{\ell+1}$ for $0 \leq \ell \leq \frac{N}{2} - 1$.

Putting $y = 1/2 - 1/N$ into (2.11), we have

$$\begin{aligned}
 h\left(\frac{1}{2} - \frac{1}{N}\right) &\geq x \tanh x \left(\frac{1}{2} - \frac{1}{N}\right) - \ln \frac{1 - \frac{1}{N}}{\frac{1}{N}} - \varepsilon \\
 &= x \frac{\tanh \frac{x}{2} - \tanh \frac{x}{N}}{1 - \tanh \frac{x}{2} \tanh \frac{x}{N}} - \ln N(1 - \frac{1}{N}) - \varepsilon \\
 &\geq x(\tanh \frac{x}{2} - \frac{x}{N}) - \ln N - \varepsilon
 \end{aligned} \tag{2.15}$$

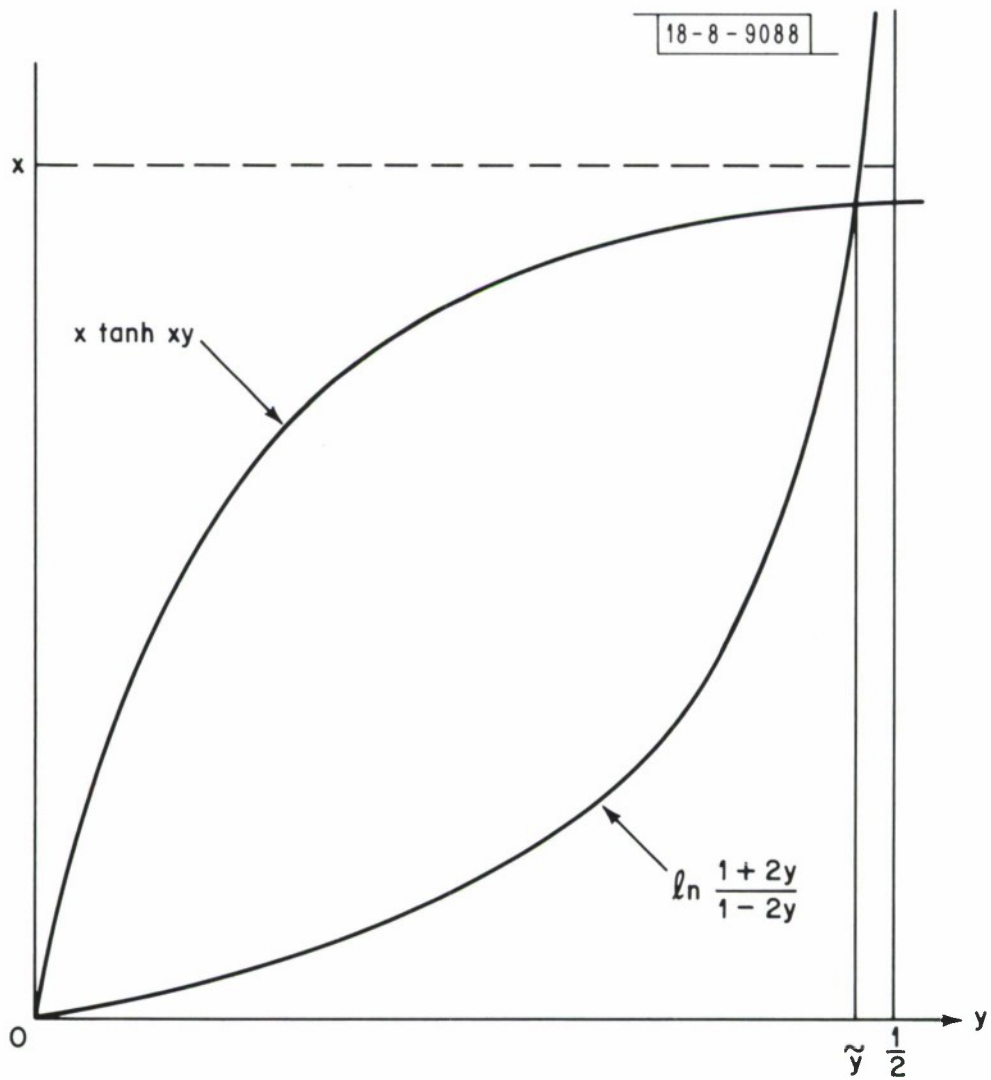


Fig. 1

For the last inequality we used $1 \geq \tanh \frac{x}{2} \tanh \frac{x}{N} \geq 0$,
 $\tanh \frac{x}{N} \leq \frac{x}{N}$. Clearly then

$$h\left(\frac{1}{2} - \frac{1}{N}\right) > 0 \text{ for } x > 200 \text{ and } N < e^{199}, \text{ but } x^2/N \ll 1 \quad (2.16)$$

the range discussed below Eq. (IA.17).

We now find an upper bound to the other positive root, y_0 ,
of $h_0(y) = 0$. Put

$$\ln^{1+2y} + \varepsilon \equiv g(y) \quad (2.17)$$

so y_0 satisfies

$$x \tanh xy_0 = g(y_0) \quad (2.18)$$

and is, by definition, the smallest positive root. Now
 $g(0) = \varepsilon > 0$, $\tanh xy = 0$ at $y = 0$, and both $\tanh xy$ and $g(y)$
monotonically increase with y . Hence if we replace $\tanh xy$ by
 $\bar{t}(y) < \tanh xy$ and replace $g(y)$ by $\bar{g}(y) > g(y)$, then

$$x\bar{t}(y_u) = \bar{g}(y_u) \quad (2.19)$$

where

$$y_u > y_0 \quad (2.20)$$

(The latter may be seen very simply by graphical means.)

Using (IA.27), we will choose

$$\bar{t}(y) = xy - \frac{1}{3} x^3 y^3 \quad (2.21)$$

Also

$$-\ln(1-2y) \leq \frac{2y}{1-2y}, \quad y \geq 0 \quad (2.22)$$

Proof: $f(x) \equiv \frac{x}{1-x} + \ln(1-x)$; then $f(0) = 0$

$$f'(x) = \frac{x}{(1-x)^2} > 0 \text{ for } x > 0$$

$$\therefore f(x) \geq 0 \text{ for } x \geq 0$$

So, using in addition $\ln(1+2y) \leq 2y$, we can choose

$$\bar{g}(y) = 4y \frac{1-y}{1-2y} + \varepsilon \quad (2.23)$$

Thus y_u satisfies $x\bar{t}(y) = \bar{g}(y)$, which can be written

$$(x^2 - 4 + 2\varepsilon)y = (2x^2 - 4)y^2 + \frac{1}{3}x^4y^3 - \frac{2}{3}x^4y^4 + \varepsilon \equiv \bar{h}(y) \quad (2.24)$$

Again: the l.h.s. increases monotonically and is zero at $y = 0$, while $\bar{h}(0) = \varepsilon > 0$, so that increasing the r.h.s., $\bar{h}(y)$, will increase the smallest positive root. Clearly, for $y \leq 1$,

$$\bar{h}(y) \leq (2x^2 - 4)y^2 + \frac{1}{3}x^4y^2 + \varepsilon$$

so that y_u (actually bigger than the y_u satisfying (2.24)) satisfies

$$(2x^2 - 4 + \frac{1}{3}x^4)y^2 - (x^2 - 4 + 2\varepsilon)y + \varepsilon = 0 \quad (2.25)$$

We want the root that $\rightarrow 0$ as $\varepsilon \rightarrow 0$: So

$$y_u = \frac{(x^2 - 4 + 2\epsilon)(1 - \sqrt{1 - \Gamma})}{2(2x^2 - 4 + \frac{1}{3}x^4)} \quad (2.26)$$

with

$$\Gamma \equiv \frac{4\epsilon (\frac{1}{3}x^4 + 2x^2 - 4)}{(x^2 - 4 + 2\epsilon)^2} < 1 \text{ for } x \gg 200, \epsilon \sim \frac{x^2}{N} \ll 1 \quad (2.27)$$

Also $\sqrt{1 - \Gamma} > 1 - \Gamma$ for $0 < \Gamma < 1$, and $x^2 - 4 + 2\epsilon > 0$ for our parameter range, so that

$$y_u < \frac{x^2 - 4 + 2\epsilon}{2(\frac{1}{3}x^4 + 2x^2 - 4)} = \frac{2\epsilon}{x^2} \frac{1}{1 - \frac{4}{x^2} + \frac{2\epsilon}{x^2}} \equiv y_o^u \quad (2.28)$$

So

$$2 - N y_o^u = \frac{1 - \frac{10}{x^2} + \frac{4\epsilon}{x^2} - \frac{2x}{3N}}{1 - \frac{4}{x^2} + \frac{2\epsilon}{x^2}} > 0 \text{ for the range of interest} \quad (2.29)$$

i.e.,

$$N y_o^u < 2 \quad (2.30)$$

which is the desired upper bound on y_o .

For g_o , we use $\cosh x > 1 + \frac{x^2}{2}$ and $\frac{x}{1+x} < \ln(1+x) < x$ for $x < 1$, and find that

$$g_0 = e^{N \ln \cosh \frac{x}{N} - \ln (1 + \frac{2}{N})} \geq e^{\frac{x^2/2N}{1 + x^2/2N^2} \left[1 - \frac{4}{x^2} (1 + \frac{x^2}{2N^2}) \right]} \quad (2.31)$$

so that $g_0 > 1$ for $x \geq 200$ and $x^2/N \ll 1$.

Again

$$\begin{aligned} g_1 &= (\cosh \frac{x}{N})^N (1 + \tanh^2 \frac{x}{N})^N \frac{\frac{N}{2} - 1}{\frac{N}{2} + 2} \\ &> (\cosh \frac{x}{N})^N (1 - \frac{6}{N}) \\ &> e^{\frac{x^2/2N}{1 + x^2/2N^2} - \frac{6/N}{1-6/N}} \\ &= e^{\frac{1}{N} \left[(\frac{x^2}{2} - 6) - \frac{3x^2}{N} (1 + \frac{1}{N}) \right] / (1 + \frac{x^2}{2N^2}) (1 - \frac{6}{N})} \\ &> 1 \text{ for } x \geq 200, \frac{x^2}{N} \ll 1 \end{aligned}$$

(Actually, to a very good approximation,

$$g_1 \cong e^{\frac{x^2}{2N} + \frac{x^2}{N} - \frac{6}{N}} = e^{\frac{1}{N} (\frac{3x^2}{2} - 6)} \quad (> 1 \text{ for } x > 2, \text{ which is the critical value in the THFA.})$$

DOCUMENT CONTROL DATA - R&D		
(Security classification of title, body of abstract and indexing annotation must be entered when the overall report is classified)		
1. ORIGINATING ACTIVITY (Corporate author) Lincoln Laboratory, M.I.T.		2a. REPORT SECURITY CLASSIFICATION Unclassified
		2b. GROUP None
3. REPORT TITLE On the Theory of Localized One-Electron States in Perfect Crystals		
4. DESCRIPTIVE NOTES (Type of report and inclusive dates) Technical Note		
5. AUTHOR(S) (Last name, first name, initial) Kaplan, Thomas A. and Argyres, Petros N.		
6. REPORT DATE 1 September 1970	7a. TOTAL NO. OF PAGES 14	7b. NO. OF REFS 2
8a. CONTRACT OR GRANT NO. AF 19(628)-5167		9a. ORIGINATOR'S REPORT NUMBER(S) Technical Note 1970-27
b. PROJECT NO. 649L		9b. OTHER REPORT NO(S) (Any other numbers that may be assigned this report) ESD-TR-70-245
c.		
d.		
10. AVAILABILITY/LIMITATION NOTICES This document has been approved for public release and sale; its distribution is unlimited.		
11. SUPPLEMENTARY NOTES None	12. SPONSORING MILITARY ACTIVITY Air Force Systems Command, USAF	
13. ABSTRACT <p>In a recent paper a proof was given that for a perfect crystal of hydrogen atoms, described within a certain model, the free energy corresponding to localized one-electron wave-functions was less than that corresponding to spatially extended one-electron functions. That proof, however, depended on the assumption that the summand a_ℓ appearing in the partition function for the extended solutions monotonically increases with ℓ for $\ell \geq 0$. The proof of this monotonicity is given here.</p>		
14. KEY WORDS crystal structure hydrogen atoms free energy		